GS358

Dual Operational Amplifiers

JAN. 2010

Product Description

The GS358 consists of two independent, high gain, internally frequency compensated operational amplifiers which were designed specifically to operate from a single power supply over a wide range of voltages.

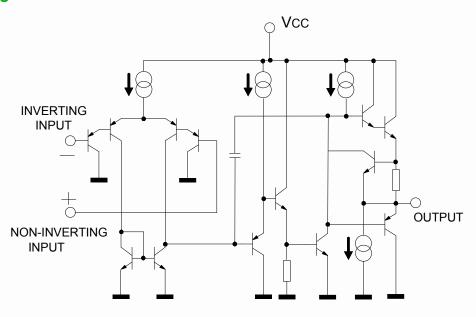
Operation from split power supplies is also possible and the low power supply current drains in independent of the magnitude of the power supply voltage.

Application areas include transducer amplifiers, dc gain blocks and all the conventional op amp circuits, which now can be more easily implemented in single power supply systems. For example, the GS358 can be directly operated off of the standard +5V power supply voltage which is used in digital systems and will easily provide the required interface electronics without requiring the additional ±15V power supplies.

Features

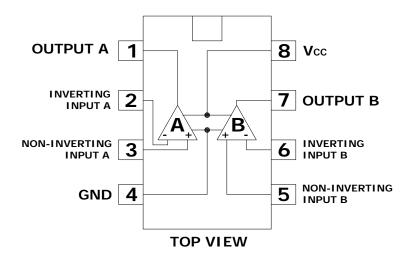
- Wide range of supply voltages 3V to 30V
- Low supply current drain independent of supply
- voltage 0.7mA (TYP.)
- Low input biasing current
- Low input offset voltage and offset current
- Input common-mode voltage range includes
- ground
- Differential input voltage range equal to the
- power supply voltage
- DC voltage gain: 100V/mV TYP.
- Internally frequency compensation
- RoHS Compliant, 100%Pb & Halogen Free

Block Diagram

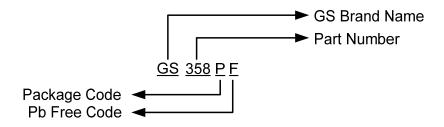




Pin Assignments

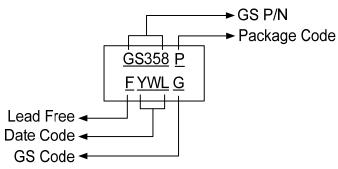


Ordering Information



Device	Package
GS358PF	DIP-8
GS358SF	SOP-8

Marking Information





GS3358

Absolute Maximum Ratings

Symbol	Parameter	Valu	Unit	
V _{CC}	Single Supply	32	2	V
V _{CC} , V _{EE}	Split Supply	±10	6	V
V _{IDR}	Input Differential Voltage Range	±32	2	V
los	Output Short-circuit to GND	Continuous		
TJ	Junction Temperature	150		°C
T _{STG}	Storage Temperature Range	-65 to +150		°C
T _A	Operating Ambient Temperature Range 0 to 70		°C	
θја	Thermal Resistance (Junction to Ambient)	DIP-8	125	°C/W
	Thermal Resistance (Junction to Ambient)	SOP-8	160	
θјς	Thormal Posistance (Junction to Coss)	DIP-8	42	°C
OJC	Thermal Resistance (Junction to Case)	SOP-8	22	
ESD	ESD Rating (HBM)	2		ΚV



Electrical Characteristics

at specified free-air temperature, V_{CC} =5V (Unless Otherwise Noted)

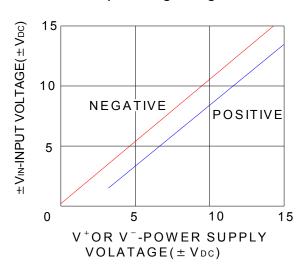
Symbol	Parameter	Test Conditions*		Min	Тур	Max	Unit	
	Input offset	V _{CC} =5V to Max.	25°C		3	7		
V _{IO}	voltage	V _{IC} =V _{ICR} min, Vo = 1.4V	Full range			9	mV	
αV_{IO}	Average temperature coefficient of input offset voltage		Full range		7		μV/°C	
I _{IO}	Input offset current	Vo = 1.4V	25°C		2	50	nA	
			Full range			150		
αl _{IO}	Average temperature coefficient of input offset current		Full range		10		pA/°C	
I _{IB}	Input bias current	Vo = 1.4V	25°C		-20	-250	nA	
чв	input bias current	VO = 1.4V	Full range			-500	107	
V _{ICR}	Common-mode input voltage	V _{CC} = 5V to MAX	25°C	0 to Vcc-1.5			V	
	ange		Full range	0 to V _{CC} -2				
		$R_L = 2k\Omega$	25°C	V _{CC} -1.5				
V _{OH}	High-level output voltage	$V_{CC} = MAX,$ $R_L = 2k\Omega$	Full range	26			V	
	Ů	$V_{CC} = MAX$, $R_L = 10k\Omega$	Full range	27	28			
V _{OL}	Low-level output voltage	R _L = 10kΩ	Full range		5	20	mV	
	Large-signal	V _{CC} = 15V	25°C	25	100		V/mV	
A _{VD}	differential voltage amplification	Vo=1V to 11V R_L =2kΩ	Full range	15				
CMRR	Common-mode rejection ratio	V_{CC} = 5V to MAX V_{IC} = V_{ICR} min	25°C	65	80		dB	
K _{SVR}	Supply voltage rejection ratio $(\Delta V_{cc}/\Delta V_{lo})$	V _{CC} = 5V to MAX	25°C	65	100		dB	
V _{O1} /V _{O2}	Crosstalk attenuation	f = 1k to 20k (Hz)	25°C		120		dB	
		V _{CC} = 15V,	25°C	-20	-30		mA	
		V _{ID} = 1V, Vo = 0V	Full range	-10				
lo	Output current	V _{CC} = 15V	25°C	10	20			
	,	V _{ID} = -1V, Vo = 15V	Full range	5				
		V _{ID} = -1V, Vo = 200mV	25°C	12	30		μΑ	
I _{OS}	Short-circuit output current	V _{CC} at 5V, GND at –5V, Vo = 0V	25°C		±40	±60	mA	
	Supply current	Vo =2.5V, No load	Full range		0.7	1.2		
I _{CC}	I _{CC}	Supply current (two amplifiers)	V _{CC} = MAX, Vo = 0.5Vcc, No load	Full range		1	2	mA

^{*}All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified. "MAX" V_{CC} for testing Purposes is 30V. Full range is 0°C to 70°C



Typical Performance Characteristics

Input Voltage Range





90

80 70

60

50

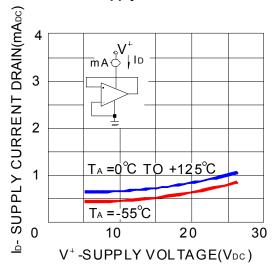
40

30

20 10 0

IB - INPUT CURRENT(nApc)

Supply Current



Voltage Gain

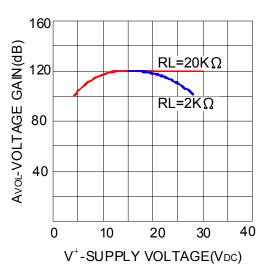
V⁺=5V_{DC}

Input Current

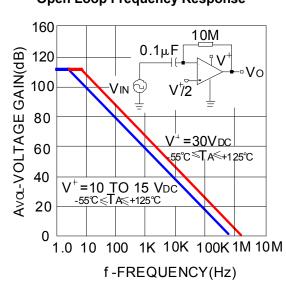
V⁺=30√_{DC}

V⁺=15V_{DC}

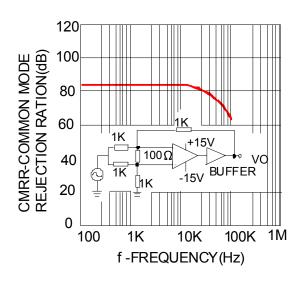
 $V_{CM} = 0 V_{DC}$



Open Loop Frequency Response

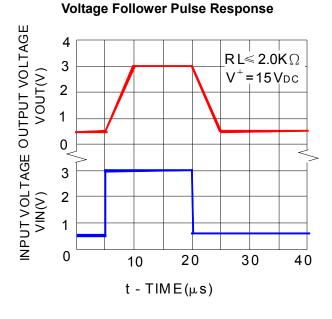


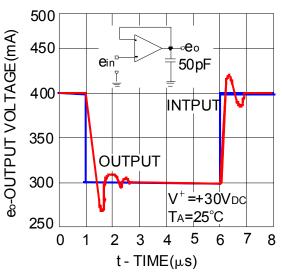
Common Mode Rejection Ratio



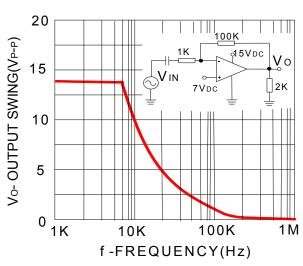


Typical Performance Characteristics (Continue)

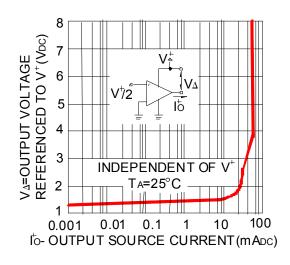




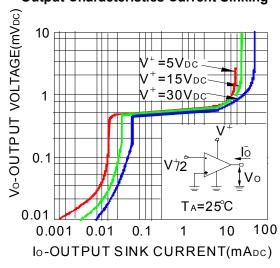
Large Signal Frequency Response



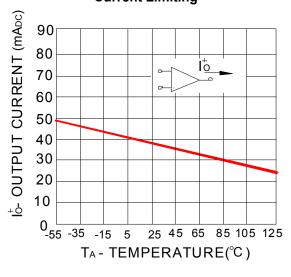
Output Characteristics Current Sourcing



Output Characteristics Current Sinking



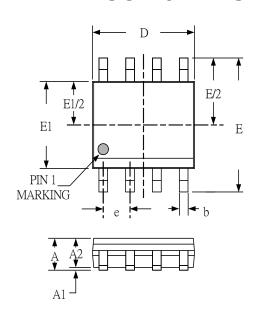
Current Limiting

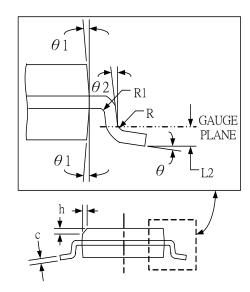




Package Dimension

SOP-8 PLASTIC PACKAGE

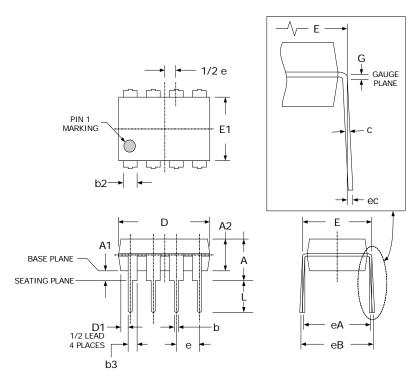




Dimensions						
SYMBOL	Millimeters		Inches			
STIMBUL	MIN	MAX	MIN	MAX		
Α	1.35	1.75	.053	.069		
A1	0.10	0.25	.004	.010		
A2	1.25	1.65	.049	.065		
b	0.31	0.51	.012	.020		
b1	0.28	0.48	.011	.019		
С	0.17	0.25	.007	.010		
D	4.90	(TYP)	.193 (TYP)			
E	6.00	(TYP)	.236 (TYP)			
E1	3.90	(TYP)	.154 (TYP)			
е	1.27	1.27 (TYP) .050 (TYP)				
L	0.40	1.27	.016	.050		
L1	1.04	(TYP)	.041 (TYP)			
L2	0.25	(TYP)	.010 (TYP)			
R	0.07	-	.003			
R1	0.07	-	.003	-		
h	0.25	0.50	.010	.020		
θ	0°	8°	0°	8°		
θ1	5°	15°	5°	15°		
θ2	0°	-	0°	-		



DIP-8 PLASTIC PACKAGE



Dimensions					
CVMDOL	Millimeters		Inches		
SYMBOL	MIN	MAX	MIN	MAX	
Α	-	5.33	-	.210	
A 1	0.38	-	.015	-	
A2	2.92	4.95	.115	.195	
b	0.36	0.56	.014	.022	
b2	1.14	1.78	.045	.070	
b3	0.76	1.14	.030	.045	
С	0.20	0.36	.008	.014	
D	9.02	10.16	.355	.400	
D1	0.13	-	.005	-	
E	7.62	8.26	.300	.325	
E1	6.10	7.11	.240	.280	
е	2.54	(TYP)	.100 (TYP)		
eA	7.62	(TYP)	.300	(TYP)	
еВ	-	10.92	-	.430	
eC	0.00	1.52	.000	.060	
L	2.92	3.81	.115	.150	
G	0.38	(TYP)	.015	(TYP)	



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